

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4178 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 9.0 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$)
- Low gate to drain charge
 $Q_{GD} = 3.7 \text{ nC TYP.}$ ($V_{DD} = 15 \text{ V}$, $I_D = 30 \text{ A}$)
- 4.5 V drive available

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SK4178(1)-S27-AY ^{Note}	Pure Sn (Tin)	Tube 75 p/tube	TO-251 (MP-3-b) typ. 0.34 g
2SK4178-ZK-E1-AY ^{Note}		Tape 2500 p/reel	TO-252 (MP-3ZK) typ. 0.27 g
2SK4178-ZK-E2-AY ^{Note}			

Note Pb-free (This product does not contain Pb in external electrode).

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	30	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 48	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 144	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	33	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \text{ to } +150$	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	23	A
Single Avalanche Energy ^{Note2}	E_{AS}	52.9	mJ

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 15 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$, $L = 0.1 \text{ mH}$

(TO-251)



(TO-252)

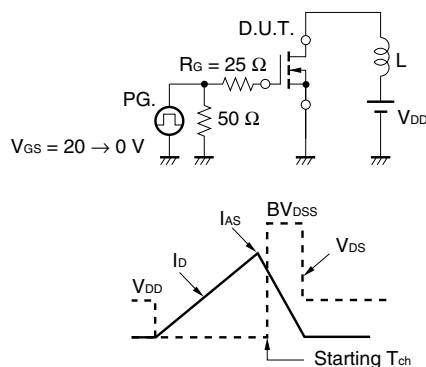


ELECTRICAL CHARACTERISTICS (T_A = 25°C)

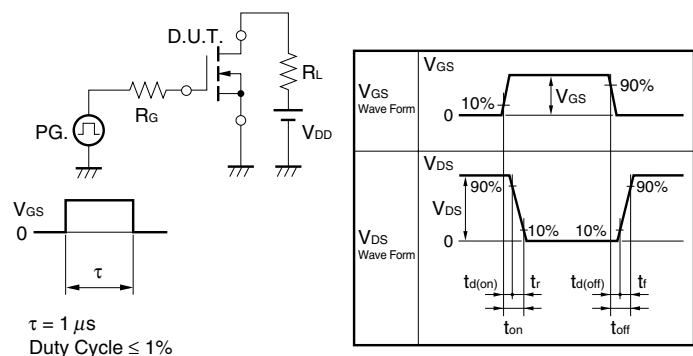
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 12 A	7	15		S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 30 A		6.8	9.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 12 A		9.8	15	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V,		1500		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		360		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		126		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 30 A,		9		ns
Rise Time	t _r	V _{GS} = 10 V,		9.7		ns
Turn-off Delay Time	t _{d(off)}	R _G = 3 Ω		32		ns
Fall Time	t _f			7.7		ns
Total Gate Charge	Q _{G1}	V _{DD} = 15 V, V _{GS} = 10 V, I _D = 30 A		24		nC
	Q _{G2}	V _{DD} = 15 V, V _{GS} = 4.5 V, I _D = 30 A		11.5		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 15 V, I _D = 30 A		3.7		nC
Gate to Drain Charge	Q _{GD}			3.7		nC
Gate Resistance	R _G			1.2		Ω
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 30 A, V _{GS} = 0 V		0.87	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, V _{GS} = 0 V,		29		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		23		nC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

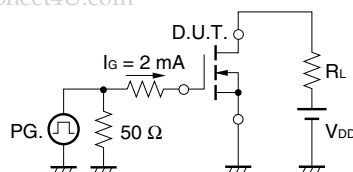


TEST CIRCUIT 2 SWITCHING TIME

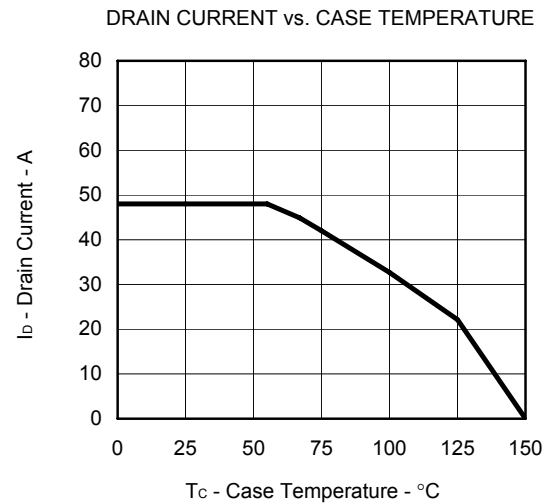
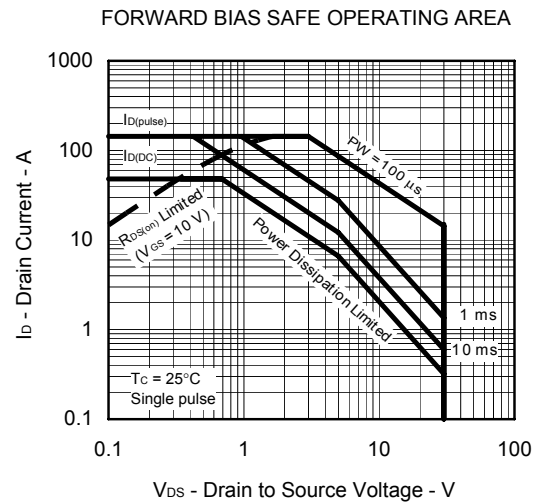
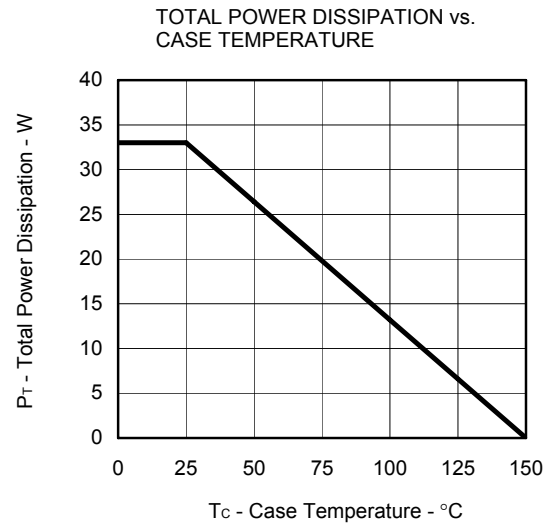
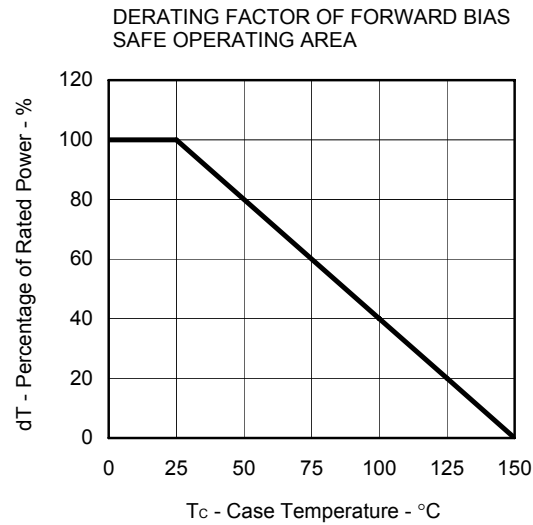


TEST CIRCUIT 3 GATE CHARGE

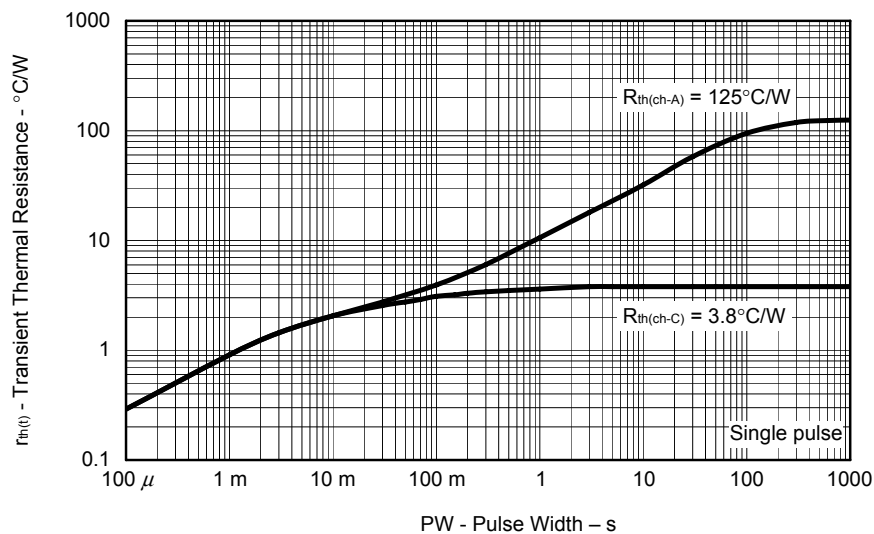
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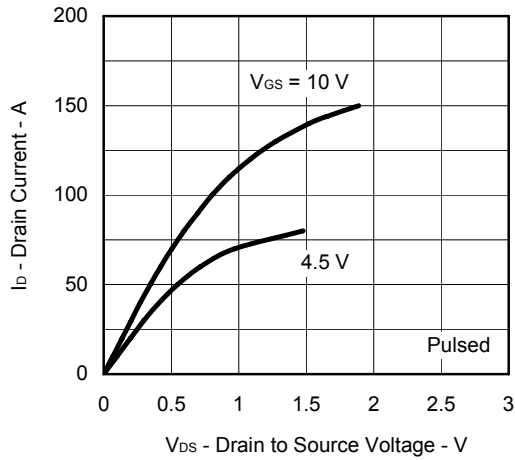
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



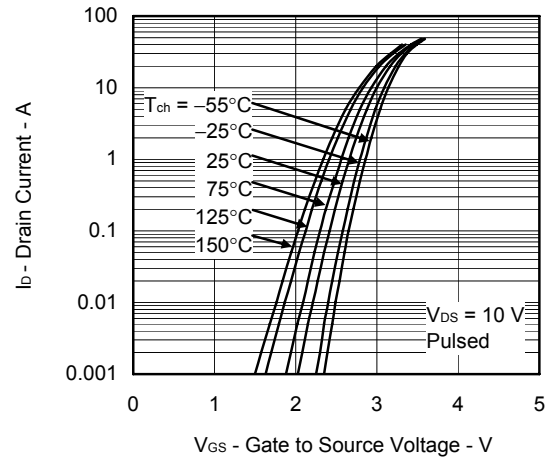
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



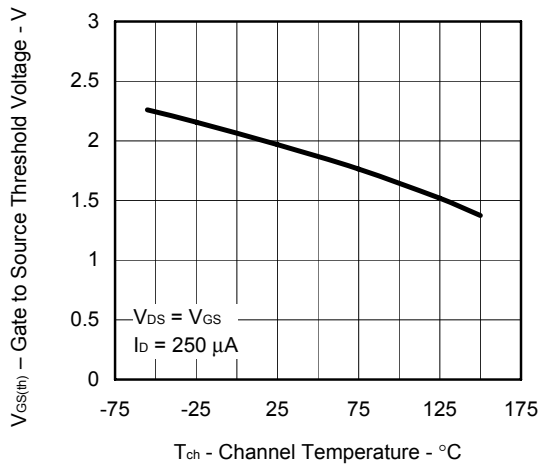
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



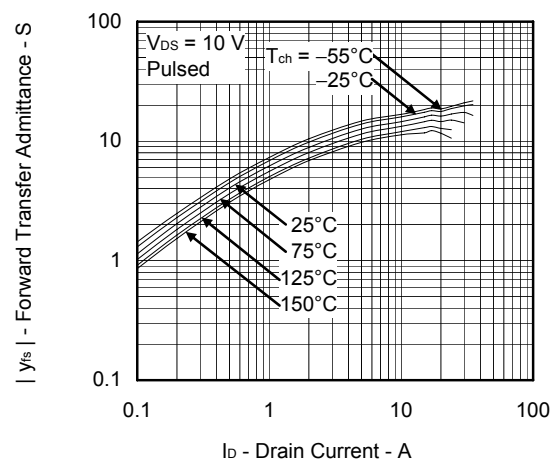
FORWARD TRANSFER CHARACTERISTICS



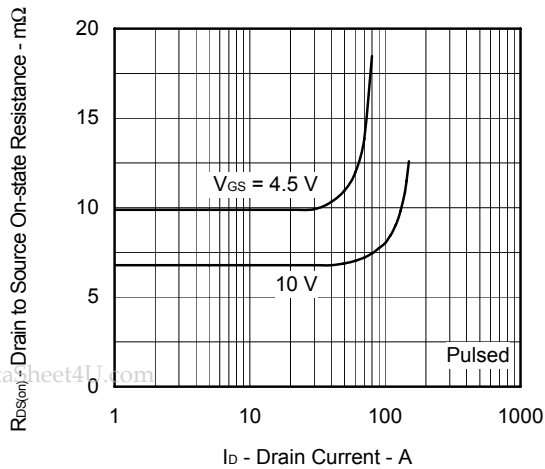
GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE



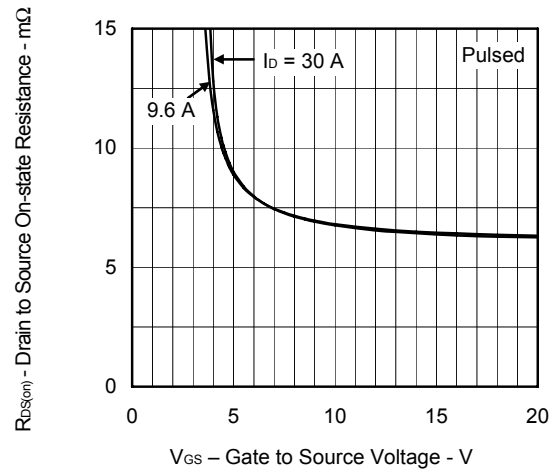
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



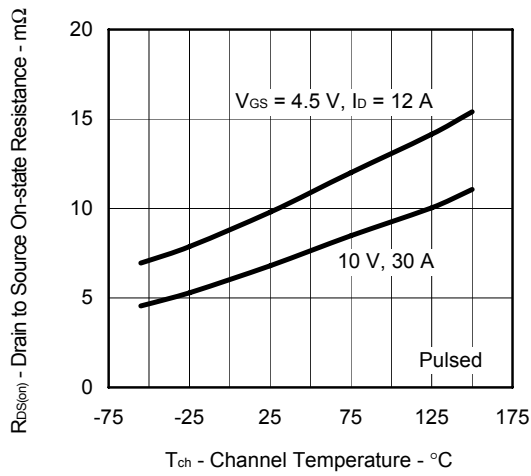
DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT



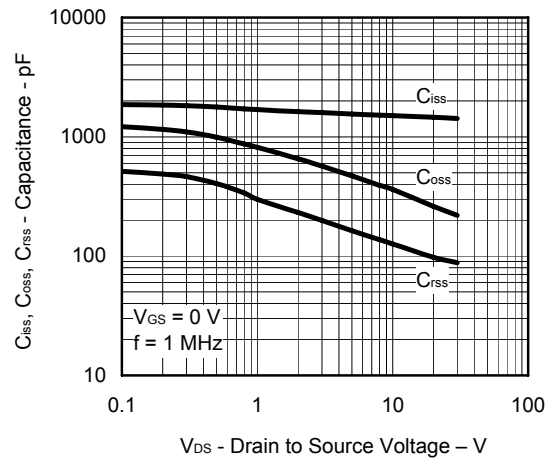
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



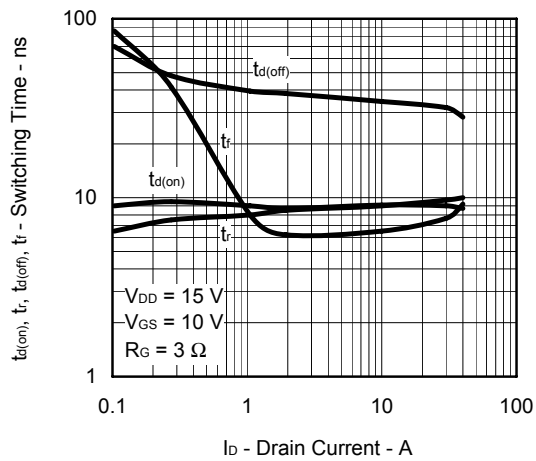
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



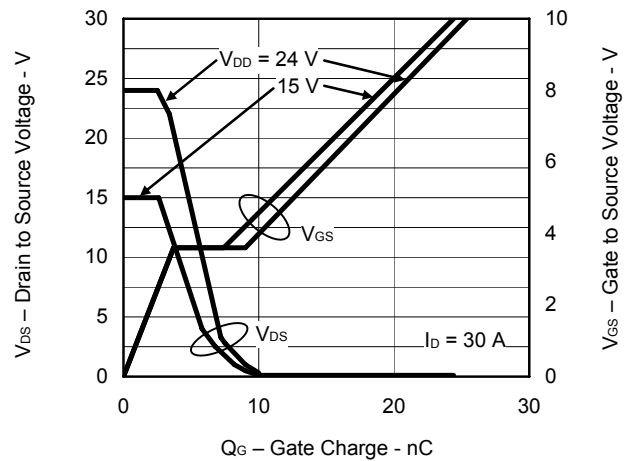
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



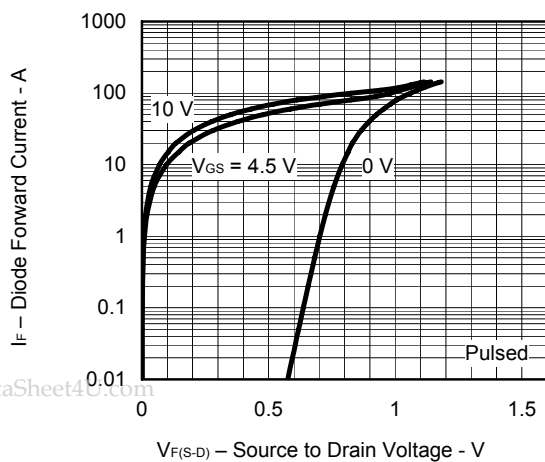
SWITCHING CHARACTERISTICS



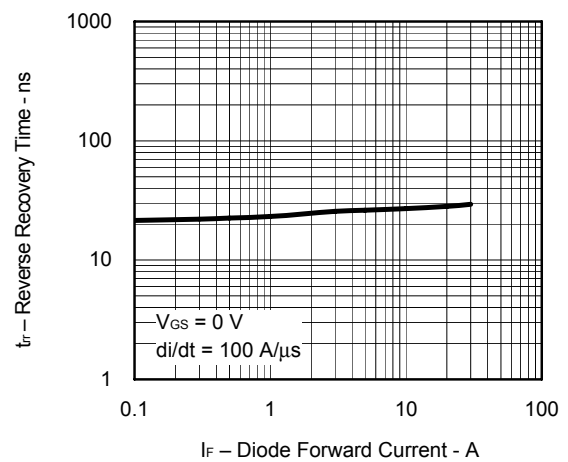
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

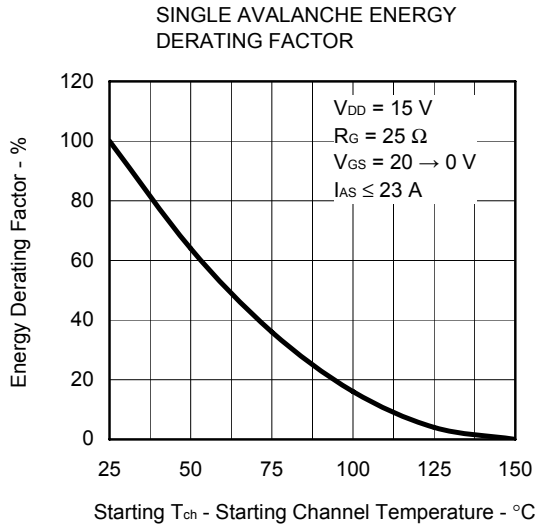
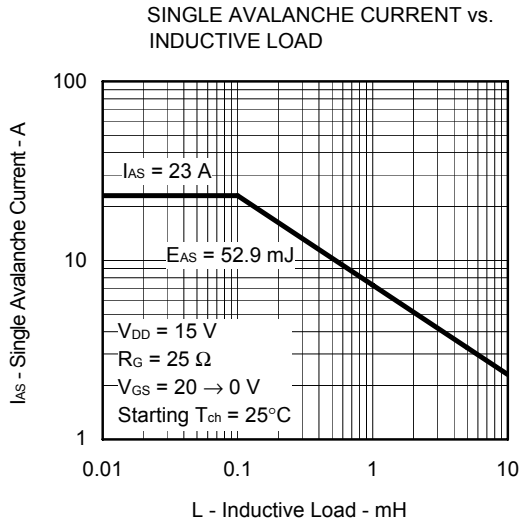


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



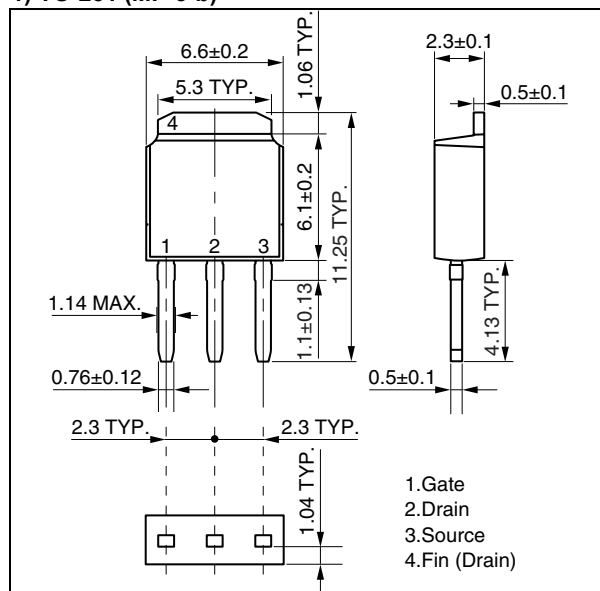
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



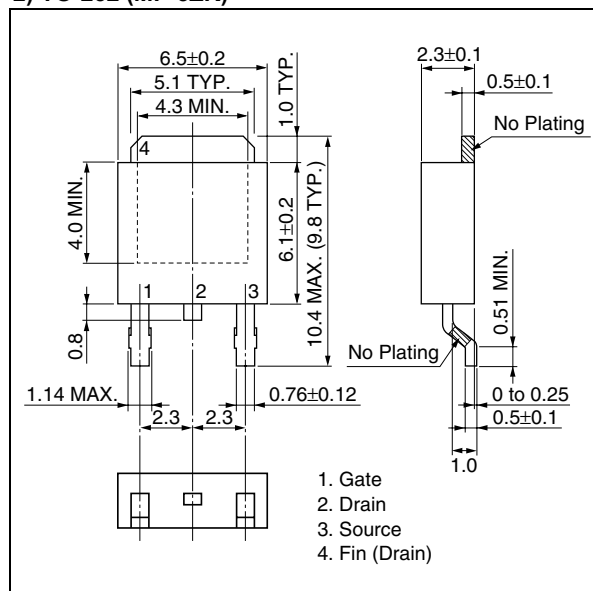


PACKAGE DRAWINGS (Unit: mm)

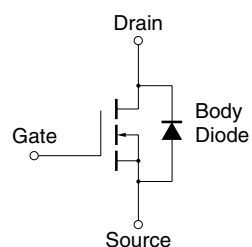
1) TO-251 (MP-3-b)



2) TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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